



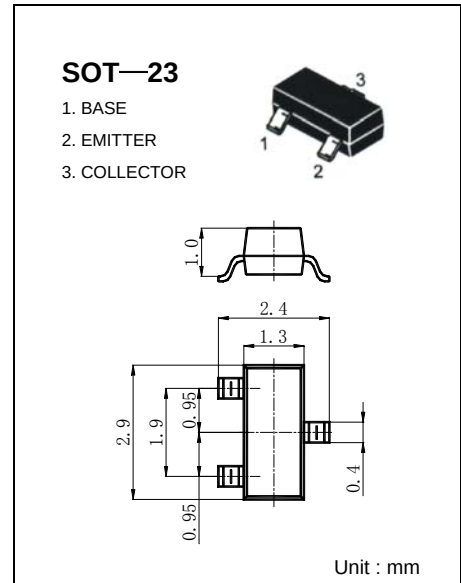
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

KTC3265 TRANSISTOR (NPN)

FEATURES

- High DC current gain: $h_{FE}=100-320$
- Complementary to kta1298



MAXIMUM RATINGS* $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	800	mA
P_C	Collector Dissipation	200	mW
T_J, T_{stg}	Junction and Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			0.1	μA
Collector cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=1\text{V}, I_C=100\text{mA}$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=20\text{mA}$			0.5	V
base-emitter voltage	$V_{BE(ON)}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$	0.5		0.8	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=10\text{mA}$ $f=100\text{MHz}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		13		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320
Marking	EO	EY

Typical Characteristics

KTC3265

